

Attorney's Docket No.: 07977/204002/US3480D1

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested.

Initially, the indication that all claims are allowable other than rejections under §112 is appreciatively noted. Claims amendments are made herein which obviate the §112 rejections.

Claims 22 and 26 stand rejected under 35 U.S.C. 112, first paragraph, as allegedly containing subject matter which was not described in the specification. Claim 22 has been amended to recite that the gate insulation film is formed of silicon oxide which is supported by page 11, lines 14-17. Claim 26 has been amended in a similar way, thus obviating the rejections.

Claims 22, 25-27, 31, 32, and 38 stand rejected under 35 U.S.C. 112, second paragraph, as allegedly being indefinite. In response, these claims are amended for definiteness. Claim 22 and others like it have been amended to specify that the first insulating film is a gate insulating film, and in this case, the silicon is oxidized to form silicon oxide.

Claim 25 has been amended to recite first and second insulating layers in order to obviate the ambiguity.

In view of the above amendments and remarks, therefore, all of the claims should be in condition for

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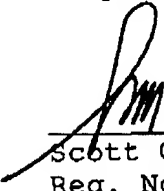
allowance. A formal notice to that effect is respectfully solicited.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date:

4/3/02



Scott C. Harris
Reg. No. 32,030

SCH/smr

Fish & Richardson P.C.
PTO Customer No. 20985
4350 La Jolla Village Drive, Suite 500
San Diego, California 92122
Telephone: (858) 678-5070
Facsimile: (858) 678-5099

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VERSION TO SHOW CHANGES MADEIn the Claims:

Claims 21, 22, 25, and 26 have been amended as follows.

21. (Amended) A semiconductor device comprising:

a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;

[an] a first insulating film formed on said gate electrode;

a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film[,] ;
and

a second insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer.

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22. (Amended) A semiconductor device according to claim 21, wherein said first insulating film [comprises] is a gate insulating film comprising silicon oxide.

25. (Amended) A semiconductor device comprising:

a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;

a [gate] first insulating film formed on said gate electrode;

a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film, and

[an] a second insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

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26. (Amended) A semiconductor device according to claim 25,
wherein said insulating film [comprises] is a gate insulating
film comprising silicon oxide.